

# Low VF and Low IR

## Next Generation Schottky Barrier Diode Achieves

Equals increased effectiveness of the power supply when placed in or near the circuit—Can extend the life of the battery! Plus Reduced heat radiation

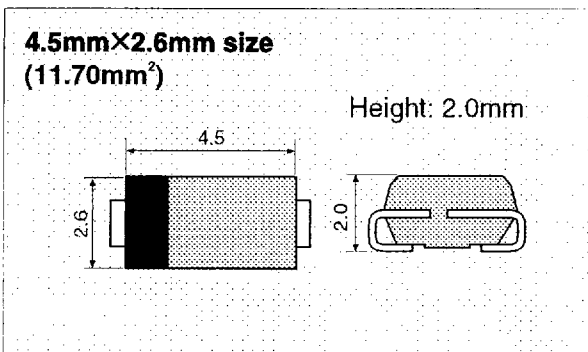


Reduce the problem of the heat radiation at the high temperature!



Improved the characteristics by changing the structure of the device.

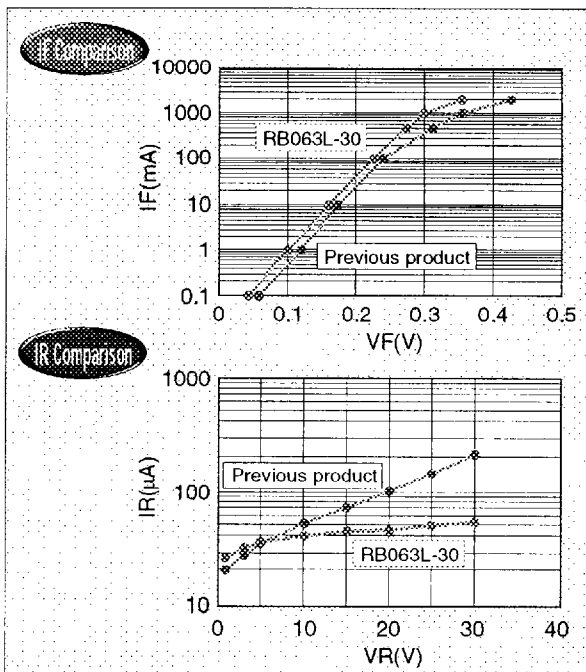
## The Evolution of the Schottky Barrier Diode



There used to be a trade-off between VF and IR—no one could have both low VF and low IR. With ROHM's original technology we have been able to have both low IR and VF without any trade-offs!

### Specification/Characteristics comparison

TYPE	Package	Io	VRM	VF(at Io/2)	IR(at VRM)
RB063L-30	PMDS [SMA]	2A	30V	0.30V	50μA
RB053L-30		3A	30V	0.34V	50μA
RB083L-20		5A	20V	0.33V	150μA



## The Evolution of the Schottky Barrier Diode

### Schottky barrier diode (Silicon Epitaxial Planer)

## RB063L-30

Low VF and IR

#### APPLICATION

General rectification

#### FEATURE

- Small power mold type (PMDS)
- High reliability
- Ultra Low VF/Low IR

#### ABSOLUTE MAXIMUM RATING (Ta=25°C)

Characteristic	Symbol	Limits
Reverse voltage (repetitive peak)	VRM	30V
Reverse voltage (DC)	VR	30V
Average rectified forward current*	Io	2A
Forward current surge peak (50Hz=)	IFSM	70A
Junction temperature	Tj	125°C
Storage temperature	Tstg	-40~125°C

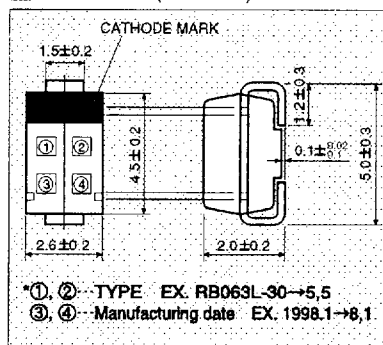
\* Glass epoxy substrate at the time of assemble 180°Half Sine Wave

#### ELECTRICAL CHARACTERISTIC (Ta=25°C)

Characteristic	Symbol	Test condition	Standard
Forward current	VF	IF=2.0A	0.395V Max.
Reverse current	IR	VR=30V	200μA Max.

\* Please pay attention to static electricity when handling.

#### DIMENSION (UNIT: mm)



Mass per piece  
69mg/pcs